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Kind regards,

Team Nexperia

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

Rev. 02 — 2 September 2009

Product data sheet

1. Product profile

1.1 General description

NPN/PNP resistor-equipped transistors

Table 1.	Product	overview
	1 I O G G G C	010111011

Type number	Package	Package		NPN/NPN complement	
	NXP	JEITA			
PEMD14	SOT666	-	PEMB14	PEMH14	
PUMD14	SOT363	SC-88	PUMB14	PUMH14	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Quick reference data					
Parameter	Conditions	Min	Тур	Max	Unit
collector-emitter voltage	open base	-	-	50	V
output current (DC)		-	-	100	mA
bias resistor 1 (input)		33	47	61	kΩ
	Parameter collector-emitter voltage output current (DC)	ParameterConditionscollector-emitter voltageopen baseoutput current (DC)	ParameterConditionsMincollector-emitter voltageopen base-output current (DC)-	ParameterConditionsMinTypcollector-emitter voltageopen baseoutput current (DC)	ParameterConditionsMinTypMaxcollector-emitter voltageopen base50output current (DC)100



006aaa269

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	R1
			1 2 3

3. Ordering information

Table 4.	Ordering	information
----------	----------	-------------

Type number	Package		
	Name	Description	Version
PEMD14	-	plastic surface mounted package; 6 leads	SOT666
PUMD14	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMD14	5B
PUMD14	T2*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	with negative polar	ity		
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1] [2]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		<u>[1]</u> <u>[2]</u> _	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

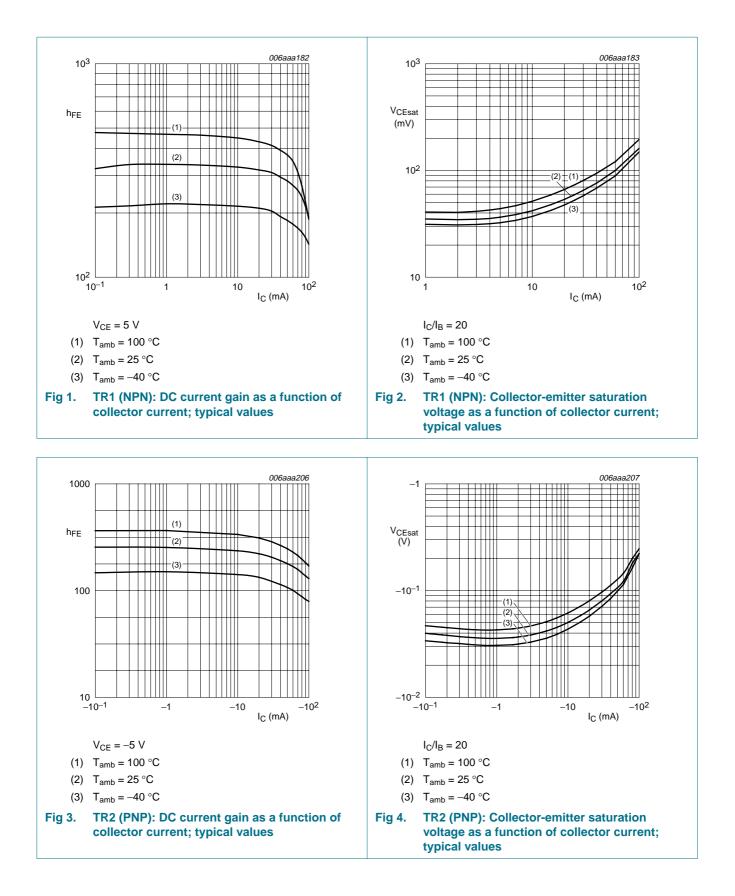
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transis	stor; for the PNP transis	tor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
	cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 10 mA; I_{B} = 0.5 mA	-	-	150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

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PEMD14; PUMD14

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open



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PEMD14; PUMD14

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

8. Package outline

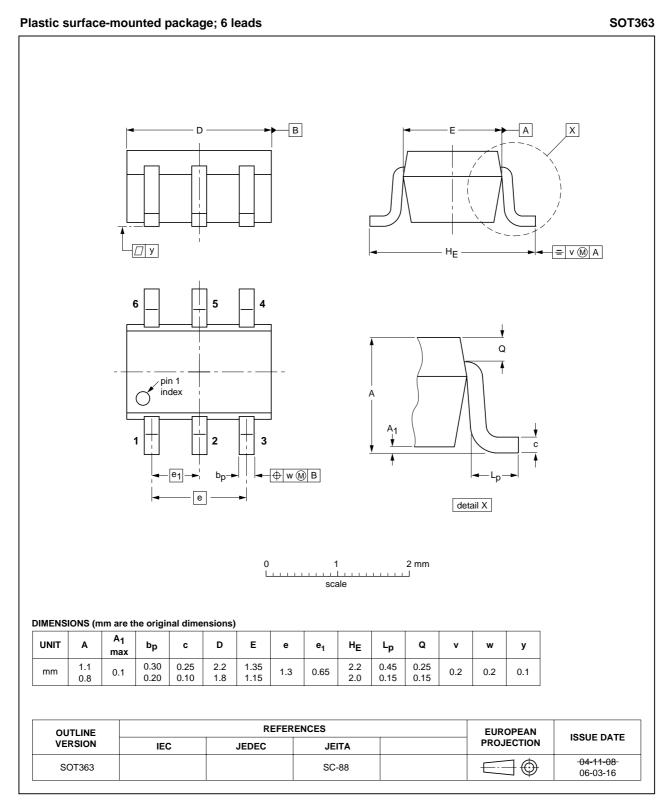


Fig 5. Package outline SOT363 (SC-88)

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

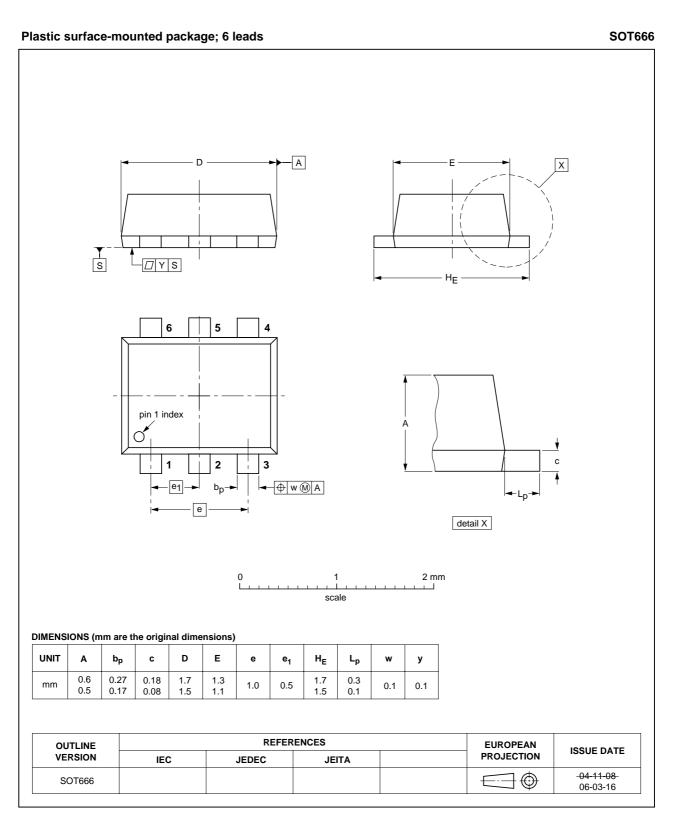


Fig 6. Package outline SOT666

PEMD14_PUMD14_2

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing of	quantity	
			3000	4000	10000
PEMD14	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T1	2 -115	-	-135
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T2	<mark>3]</mark> -125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

10. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD14_PUMD14_2	20090902	Product data sheet	-	PEMD14_PUMD14_1
Modifications:		et was changed to reflect legal definitions and disc		e NXP Semiconductors, ere made to the technical
	 Figure 5 "Pack 	kage outline SOT363 (SC	-88)": updated	
	 Figure 6 "Pack 	kage outline SOT666": up	dated	
PEMD14_PUMD14_1	20050114	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMD14_PUMD14_2
Product data sheet

NXP Semiconductors

PEMD14; PUMD14

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

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